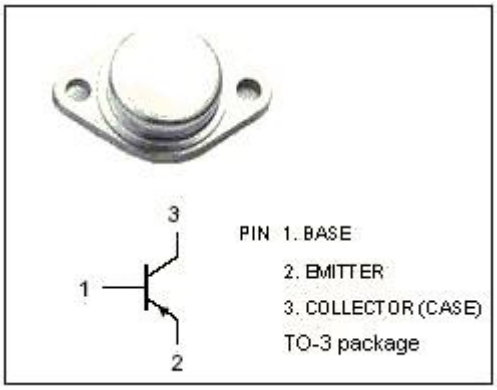
isc Silicon PNP Power Transistor 2N3172

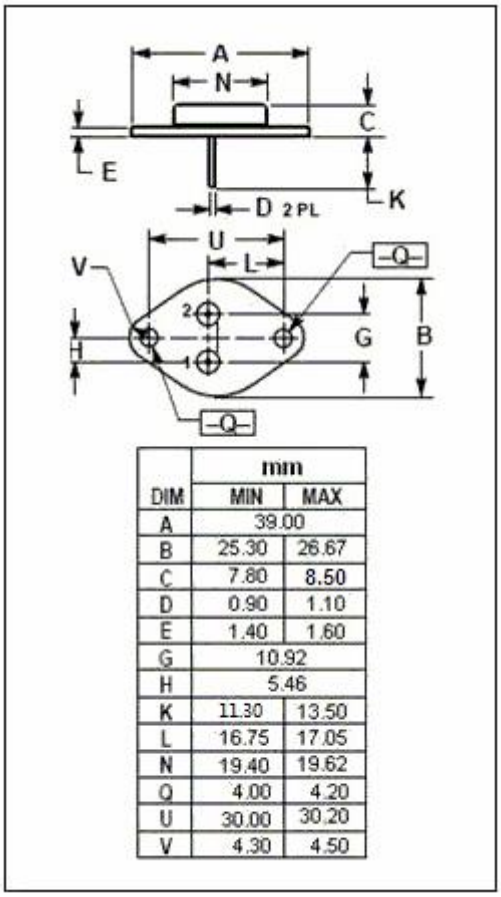
DESCRIPTION

- Excellent Safe Operating Area
- Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= -0.75V(Max)@ I_C = -1A
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- All semelab hermetically sealed products,can be processed in accordance with the requirements of BS,CECC,and JAN,JANTX and JANTXV and JAN specifications.



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-10	V
I_C	Collector Current-Continuous	-3	A
P_C	Collector Power Dissipation@T_C=25℃	75	W
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-65~+150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.67	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1A; I_B= -0.14A		-0.75	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -1A; I_B= -0.14A		-1.8	V
I_{CEO}	Collector Cutoff Current	V_{CE}= -60V; I_B=0		-0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -10V; I_C=0		-0.1	mA
h_{FE}	DC Current Gain	I_C= -1A ; V_{CE}= -3V	12	36	

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